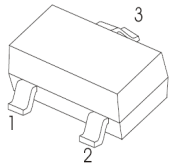
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Diodes

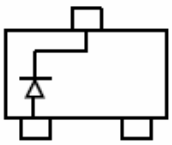
MMBD4148A/SE/CC/CA SWITCHING DIODE

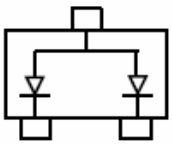
SOT-23

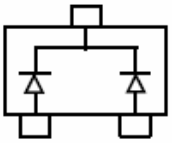


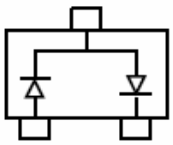
FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance









MARKING:

MMBD4148A:5H **MMBD4148CA :D6** **MMBD4148CC :D5** **MMBD4148SE :D4**

Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	200	mA
Peak Forward Surge Current @t=1.0μs @ t=1.0s	I_{FSM}	2.0 1.0	A
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

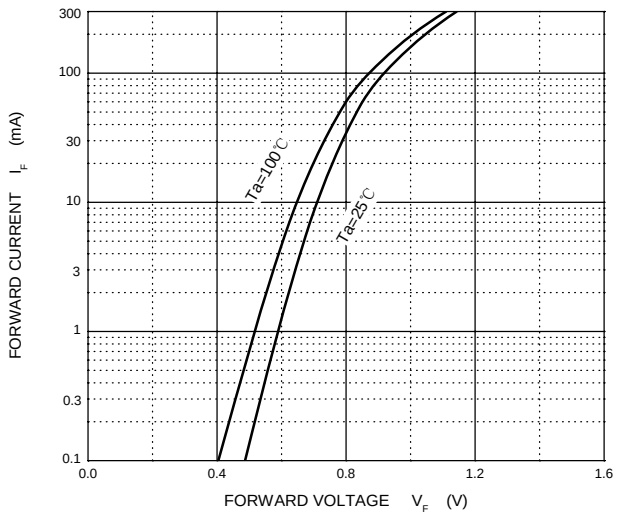
Electrical Ratings @Ta=25℃

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)1}$	100			V	I_R=100μA
	$V_{(BR)2}$	75			V	I_R=5μA
Forward voltage	V_F			1	V	I_F=10mA
Reverse current	I_{R1}			5	μA	V_R=75V
	I_{R2}			25	nA	V_R=25V
Capacitance between terminals	C_T			4	pF	V_R=0V,f=1MHz
Reverse recovery time	t_{rr}			4	ns	I_F=I_R=10mA, V_R=6V, Irr=0.1XI_R,R_L=100Ω

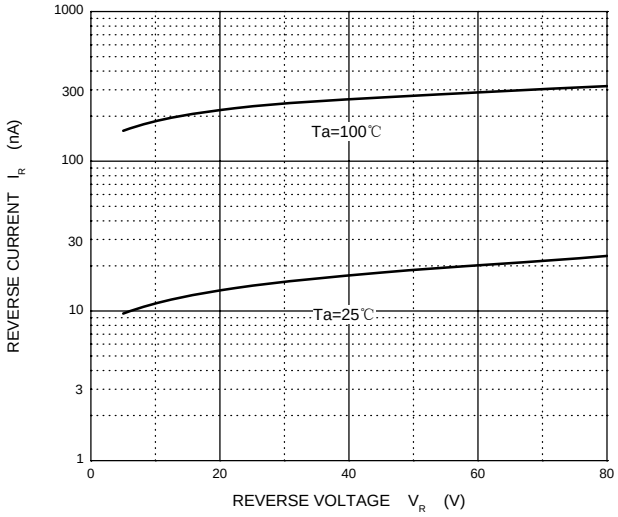
A,May,2011

Typical Characteristics MMBD4148CA

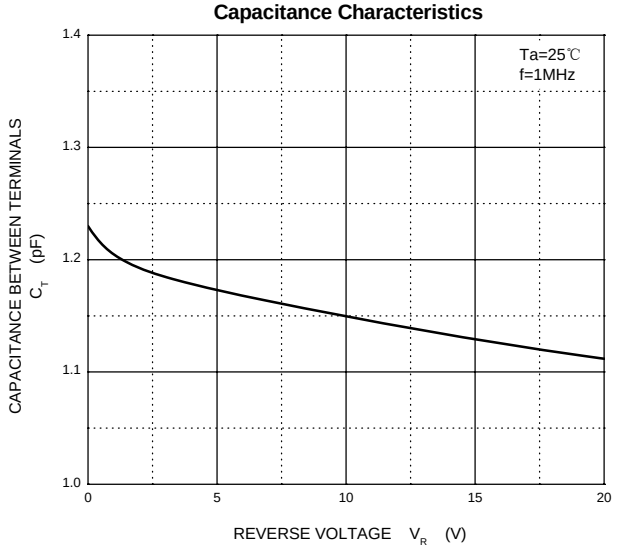
Forward Characteristics



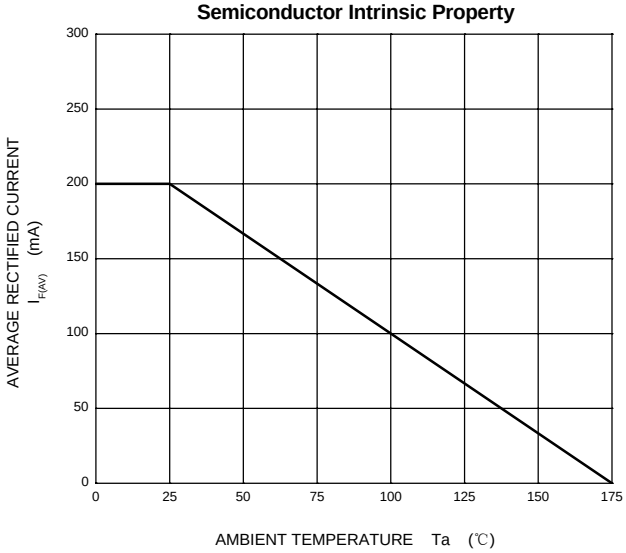
Reverse Characteristics



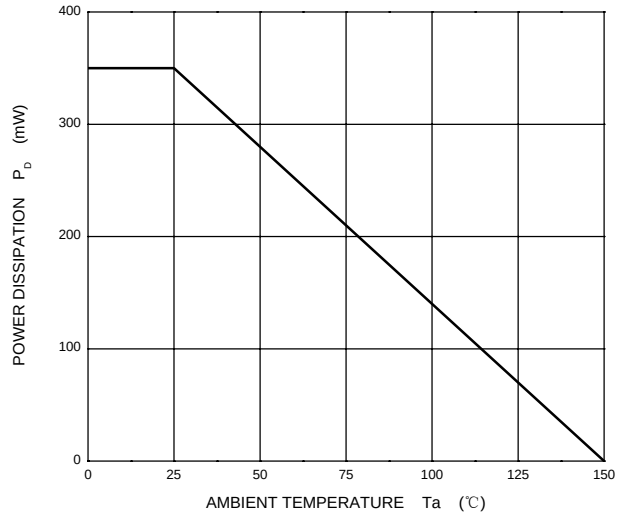
Capacitance Characteristics



Semiconductor Intrinsic Property



Power Derating Curve



A,May,2011